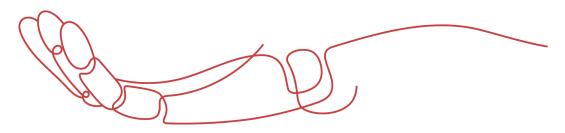


PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at

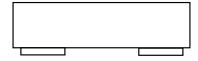


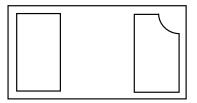
Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



ESD Protector

- Feature
- 100W peak pulse power per line (t_P = 8/20µs)
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±15KV(air), ±8KV(contact);
 IEC61000-4-4 (EFT) 40A (5/50ns)





■ Simplified outline(DFN1006-2L)

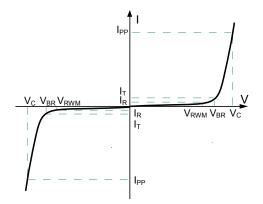
- Mechanical Characteristics
- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil
- Applications
- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Ver.1.0



Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I⊤		
Ι _Τ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
I _F	Forward Current		
V _F	Forward Voltage @ I _F		



■ Electrical characteristics per line@25°C (unless otherwise specified)

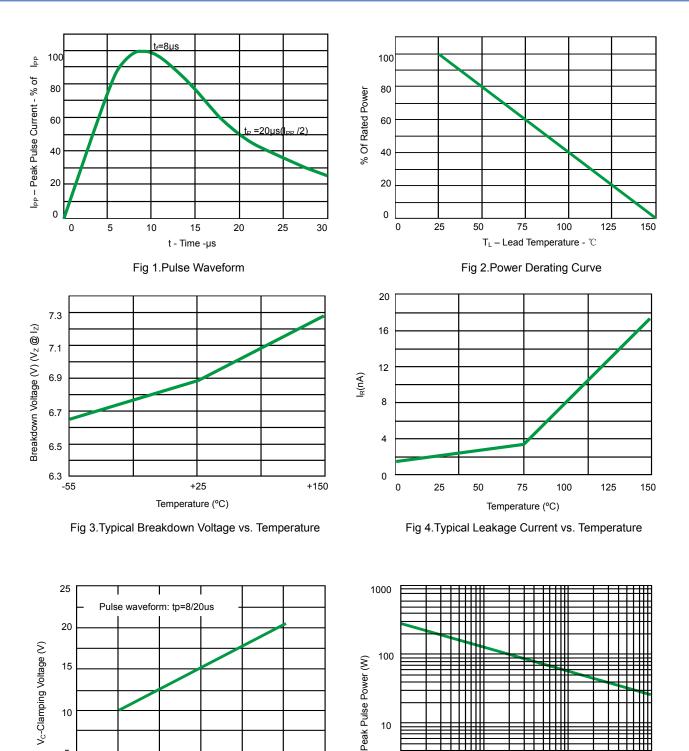
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				5	V
Breakdown Voltage	V _{BR}	I _t = 1mA	5.6		8.5	V
Reverse Leakage Current	I _R	V _{RWM} = 5V T=25°C			1.0	μA
Maximum Reverse Peak Pulse Current	I _{PP}			5.5		А
Clamping Voltage	Vc	I _{PP} =1A			10	V
Clamping Voltage	Vc	I _{PP} =3A			15	V
Clamping Voltage	Vc	I _{PP} =5A			21	V
Junction Capacitance	Cj	V _R =0V f = 1MHz		0.3		pF

■ Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20µs)	P _{pp}	100	W
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

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IPP-Peak pulse current (A) Fig 5. Clamping voltage vs. Peak pulse current

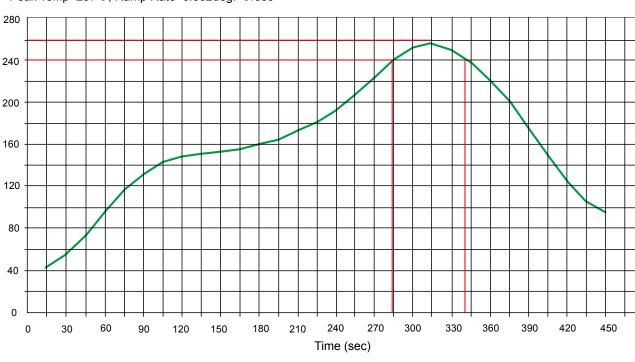
Pulse Duration(us)

Fig 6. Non-Repetitive Peak Pulse Power vs. Pulse time



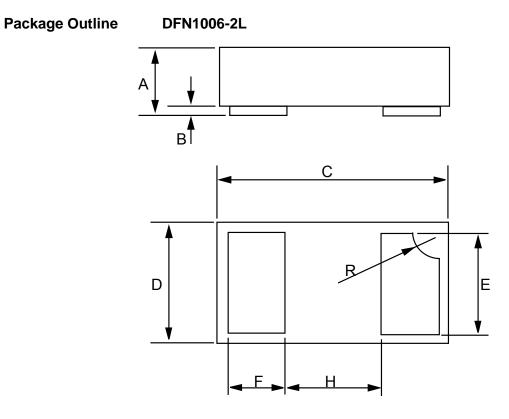
480

■ Solder Reflow Recommendation



Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec





Dim	Inc	hes	Millimeters		
	MIN	MAX	MIN	МАХ	
А	0.013	0.015	0.34	0.40	
В	0.000	0.002	0.00	0.05	
С	0.037	0.042	0.95	1.075	
D	0.021	0.026	0.55	0.675	
E	0.017	0.021	0.45	0.55	
F	0.007	0.011	0.20	0.30	
Н	0.015Typ.		0.40	Туо.	
R	0.001	0.005	0.05	0.15	





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